

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Withdrawn) A system for removing deposited material buildup from interior walls of a device that produces integrated circuit structures on semiconductor wafers, the chamber environmentally coupled to a gas source through a gaseous flow path, the system comprising:

a heat source, interposed in the gaseous flow path upstream of the chamber, the heat source adapted to heat the gas flowing from the gas supply wherein the heated gas places the atmosphere in at least part of the device at a point where sublimation or evaporation of the deposited material will occur and the system is adapted to operate to remove deposited material from the interior walls of the device by means of heated gas flow without opening the device up to atmospheric pressure.

2. (Previously Presented) A process for removing deposited material from a device, the device having interior walls upon which material is deposited, the device suitable for use in production of integrated circuit structures on semiconductor wafers, the process comprising the steps of:

creating a flow of gas through said device from a first point in the device, through an exit spaced from said first point in the device, the flow of gas creating an atmospheric pressure of about 100 Torr relative to normal atmosphere in the device;

heating the flow of gas;

sublimating or evaporating, based on a combination of said heating and the atmospheric pressure, the deposited material from the surface of the interior wall in the device into a gaseous material; and

removing the gaseous material from the device with the flow of gas,

wherein said creating, heating, sublimating or evaporating and removing all occur after the device has produced the integrated circuit structures and prior to a next time the interior walls are exposed to an environment external to the device.

3. (Previously Presented) The process of claim 2, wherein said heating is accomplished with a resistive heater.

4. (Previously Presented) The process of claim 2, wherein the device comprises a chamber, and wherein said sublimating or evaporating is directed at material deposited on an interior wall of the chamber.

5. (Previously Presented) The process of claim 2, wherein the device comprises a purge element, and wherein said sublimating or evaporating is directed at material deposited in the purge element.

6. (Original) The process of claim 2, wherein the gas is an inert gas.

7. (Original) The process of claim 6, wherein the inert gas is nitrogen.
8. (Previously Presented) A process for removing deposited material from a device suitable for use in production of integrated circuit structures on semiconductor wafers, the device having interior walls upon which material is deposited, the process comprising:
  - changing the material deposited on the interior walls of the device into a gaseous material by heating the material with a gaseous flow prior to unsealing the production device to the external environment; and
  - removing the gaseous material from the device with a gaseous flow.
9. (Previously Presented) A process for cleaning deposited material off of interior walls of a production device used in the production of semiconductor devices, the process comprising:
  - changing the material deposited on the interior walls of the device into a gaseous material by heating the material with a gaseous flow prior to unsealing the production device to the external environment; and
  - removing the gaseous material from the device with a gaseous flow.
10. (Previously Presented) A process for running a production device used in the production of semiconductor devices, the production device maintaining an internal environment sealed from an external environment when producing a batch of semiconductor devices, the production

device creating material that is deposited on interior walls of the production device when producing a batch of semiconductor devices, the process comprising the steps of:

producing a batch of semiconductor devices;

changing the material deposited on the interior walls of the device into a gaseous material by heating the material with a gaseous flow prior to unsealing the production device to the external environment; and

concurrently with said changing, removing the gaseous material from the device with a the gaseous flow.